

描述 / Descriptions

TO-220F 塑封封装 P 沟道 MOS 场效应管。P-CHANNEL MOSFET in a TO-220F Plastic Package.

特征 / Features

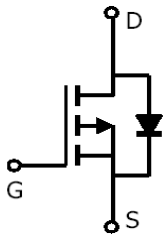
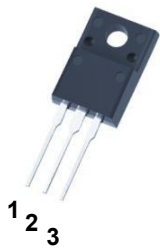
$R_{DS(on)}$ 小, 门电荷低, C_{rss} 小, 开关速度快。

Low $R_{DS(on)}$, low gate charge, low C_{rss} , fast switching.

用途 / Applications

用于低压电路如: 汽车电路、DC/DC 转换、便携式产品的电源高效转换。

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN1 : G

PIN 2 : D

PIN 3 : S

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。 See Marking Instructions.

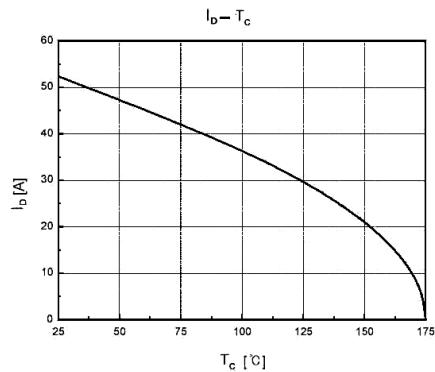
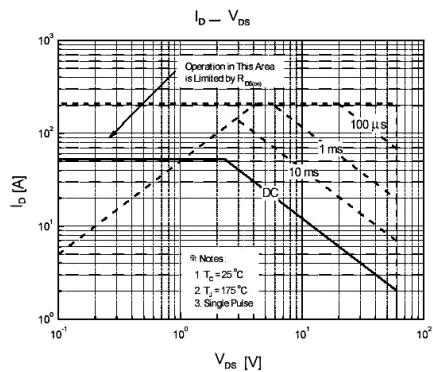
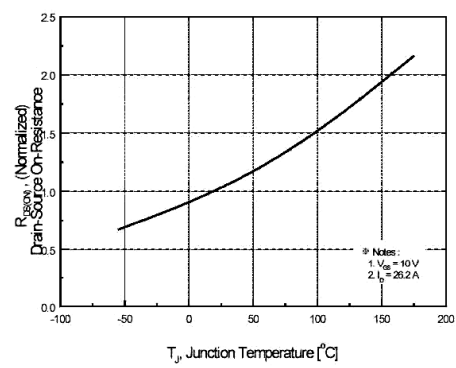
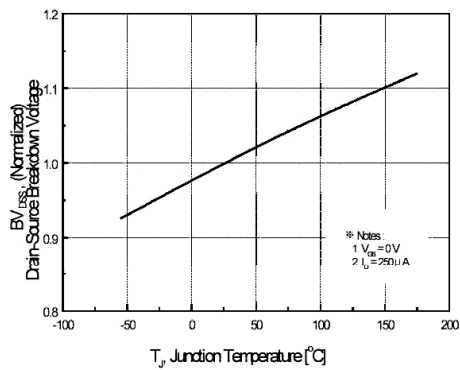
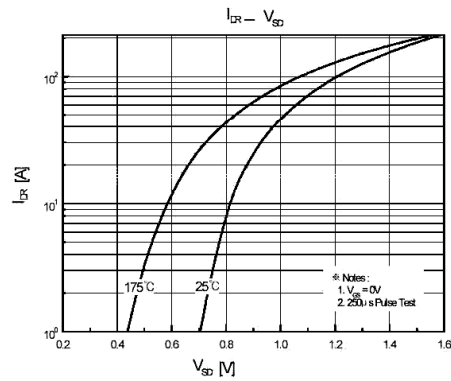
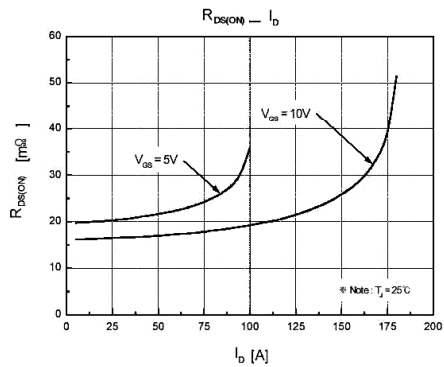
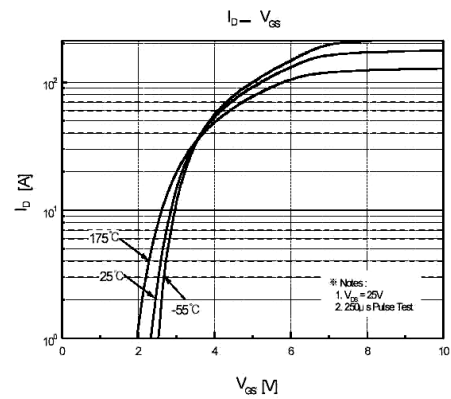
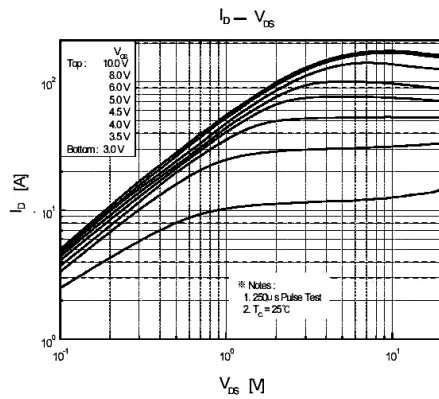

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DS}	-60	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	-50	A
Drain Current	$I_D(T_c=100^\circ\text{C})$	-35.4	A
Pulsed Drain Current	I_{DM}	-200	A
Gate-Source Voltage	V_{GS}	± 20	V
Avalanche Energy Single Pulse	E_{AS}	490	mJ
Avalanche Energy Repetitive	E_{AR}	12	mJ
Total Power Dissipation	$P_D(T_c=25^\circ\text{C})$	30	W
Junction Temperature Range	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Zero Gate Voltage Drain Current	BV_{DSS}	$V_{GS}=0V$ $I_D=-250\mu A$	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-60V$ $V_{GS}=0V$			-1.0	μA
		$V_{DS}=-48V$ $T_C=150^\circ\text{C}$			-10	
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250\mu A$	-1		-3	V
Total Gate Charge	Q_g	$V_{DS}=-48V$ $I_D=-50A$ $V_{GS}=-10V$		32	42	nC
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V$ $I_D=-25A$		0.025	0.027	Ω
Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=-50A$			-1.5	V
Input Capacitance	C_{iss}	$V_{DS}=-25V$ $V_{GS}=0V$ $f=1.0MHz$		1050	1365	pF
Output Capacitance	C_{oss}			460	600	
Reverse Transfer Capacitance	C_{rss}			70	90	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=-30V$ $I_D=-25A$ $R_G=25\Omega$		20	50	ns
Rise Time	t_r			100	210	
Turn-Off Delay Time	$t_{d(off)}$			80	170	
Fall Time	t_f			85	180	

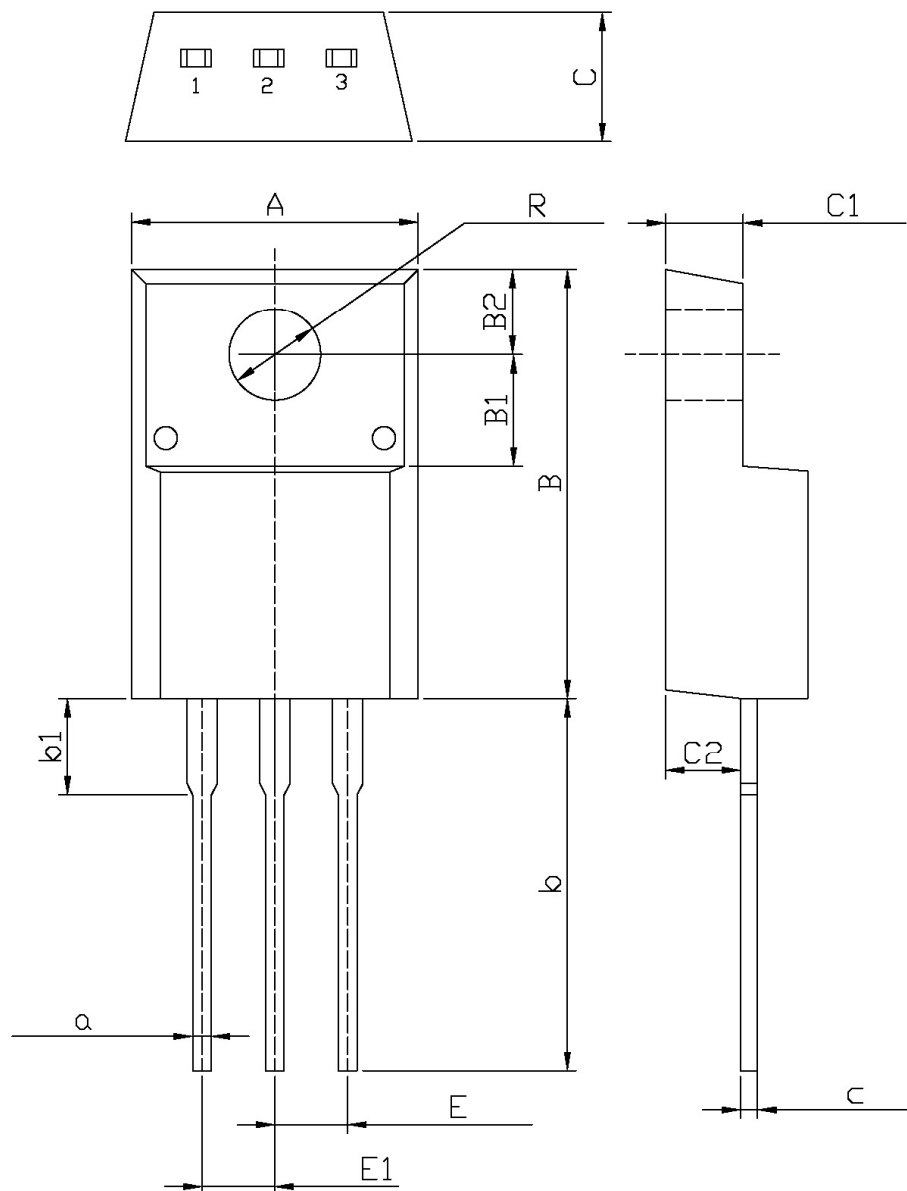
电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

T□-220F

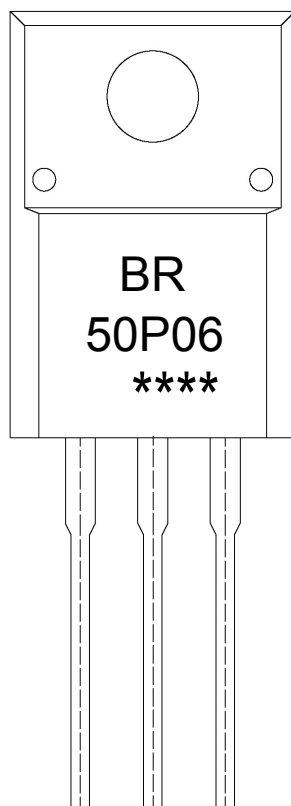
单位: mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
C	4.3	4.7	b1	2.9	3.9
A	9.7	10.3	a	0.55	0.75
B	14.7	15.3	E	2.29	2.79
B1	3.8	4.0	E1	2.29	2.79
B2	2.9	3.1	C1	2.5	2.9
R	3.0	3.4	C2	2.5	2.7
b	12.5	13.5	c	0.5	0.7



印章说明 / Marking Instructions



说明：

BR： 为公司代码

50P06： 为型号代码

****： 为生产批号代码，随生产批号变化。

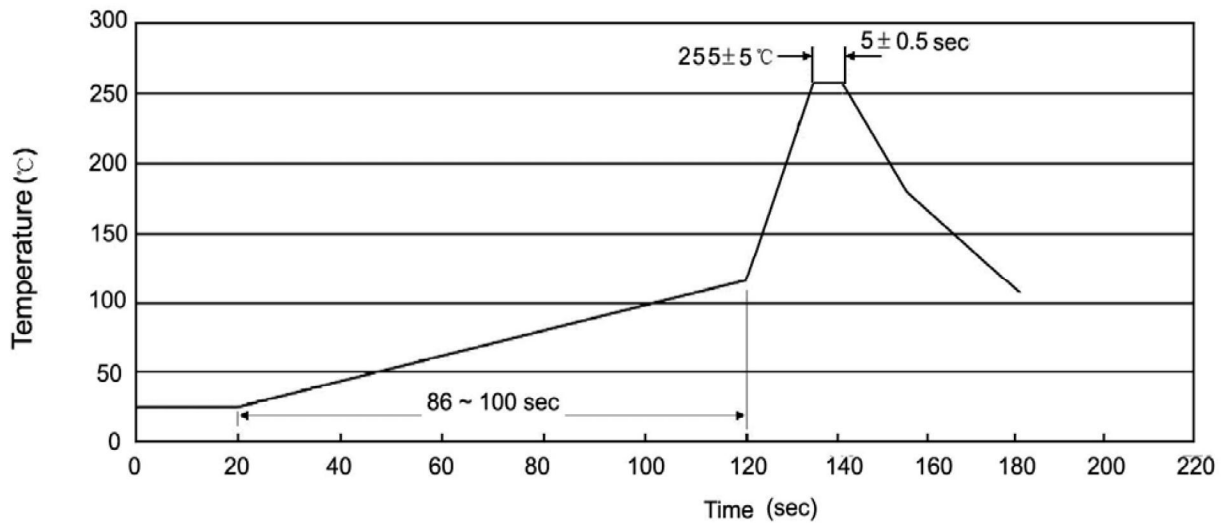
Note:

BR: Company Code

50P06: Product Type.

****: Lot No. Code, code change with Lot No.

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明：

1. 预热温度 25 ~ 150°C，时间 60 ~ 90sec;
2. 峰值温度 255±5°C，时间持续为 5±0.5sec;
3. 焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

1. Preheating: 25~150°C, Time: 60~90sec.
2. Peak Temp.: 255±5°C, Duration: 5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5°C

时间：10±1 sec.

Temp.: 270±5°C

Time: 10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-220/F	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

使用说明 / Notices